200V N-Channel Enhancement Mode MOSFET

Description

The SX2N20MI silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system

General Features

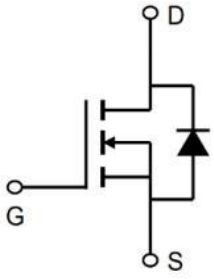
VDS =200V,ID =2A

RDS(ON) <1800mΩ@ VGS=10V

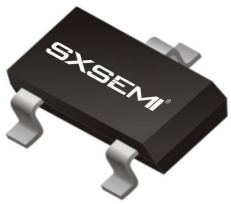
Application

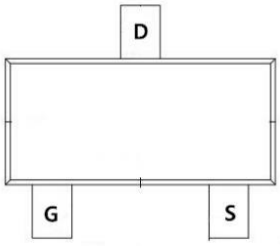
LED dimming

Emergency lamp



SOT-23-3L





Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	200	V
VGS	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	2	A
IDM	Drain Current-Pulsed (Note 1)	10	A
P_D	Maximum Power Dissipation	3	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	℃
RθJA	Thermal Resistance,Junction-to-Ambient (Note 2)	41.7	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	200	-	-	V
IDSS	Zero Gate Voltage Drain Current	V_{DS}=200V,V_{GS}=0V	-	-	1	μA
IGSS	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.0	-	3.0	V
RDS(ON)	Drain-Source On-State Resistance	V_{GS}=10V, I_D=2A	-	1400	1800	mΩ
gFS	Forward Transconductance	V_{DS}=15V,I_D=2A	-	8	-	S
C_{lss}	Input Capacitance	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	580	-	PF
Coss	Output Capacitance		-	90	-	PF
C_{rss}	Reverse Transfer Capacitance		-	3	-	PF
td(on)	Turn-on Delay Time	V_{DD}=100V, R_L=15Ω V_{GS}=10V,R_G=2.5Ω	-	10	-	nS
t_r	Turn-on Rise Time		-	12	-	nS
td(off)	Turn-Off Delay Time		-	15	-	nS
t_f	Turn-Off Fall Time		-	15	-	nS
Q_g	Total Gate Charge	V_{DS}=100V,I_D=2A, V_{GS}=10V	-	12		nC
Q_{gs}	Gate-Source Charge		-	2.5	-	nC
Q_{gd}	Gate-Drain Charge		-	3.8	-	nC
VSD	Diode Forward Voltage (Note 3)	V_{GS}=0V,I_S=2A	-	-	1.2	V
I_S	Diode Forward Current (Note 2)		-	-	2	A

Notes:

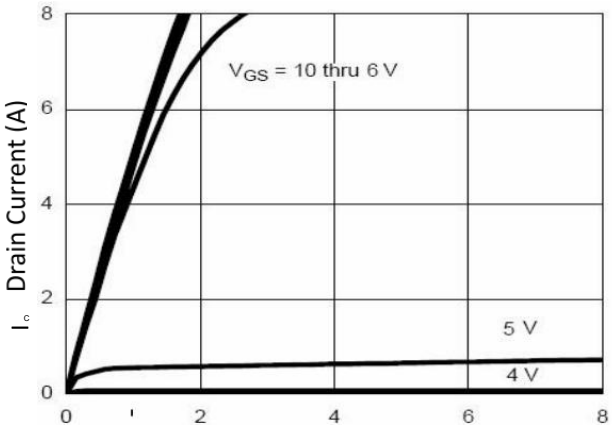
1、Repetitive Rating: Pulse width limited by maximum junction temperature.

2、Surface Mounted on FR4 Board, t ≤ 10 sec.

3、Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

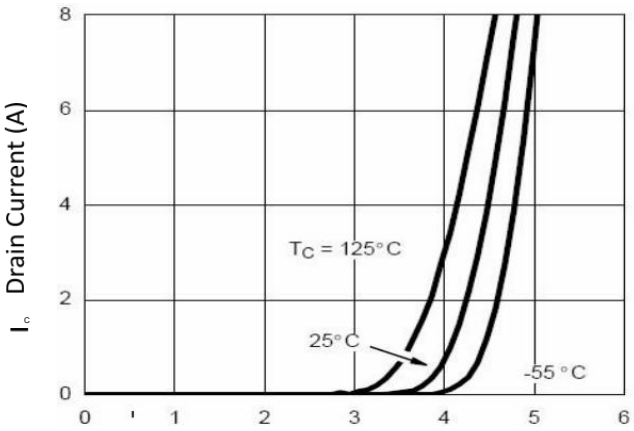
4、Guaranteed by design, not subject to production

Typical Characteristics



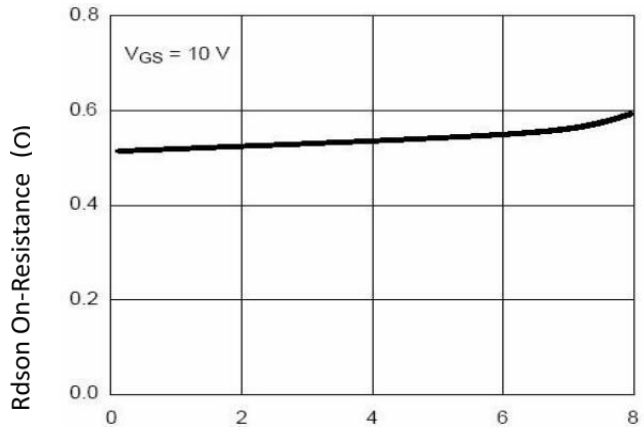
Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



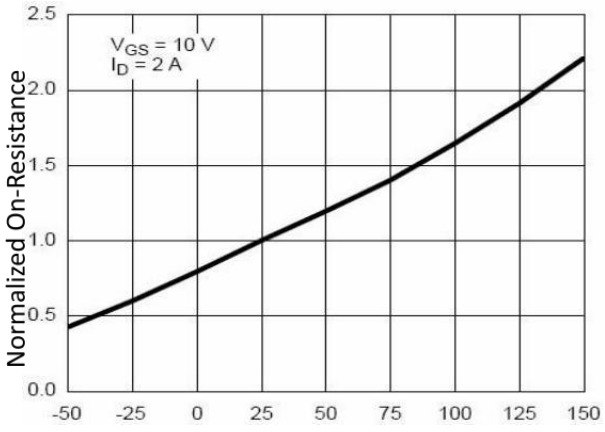
Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



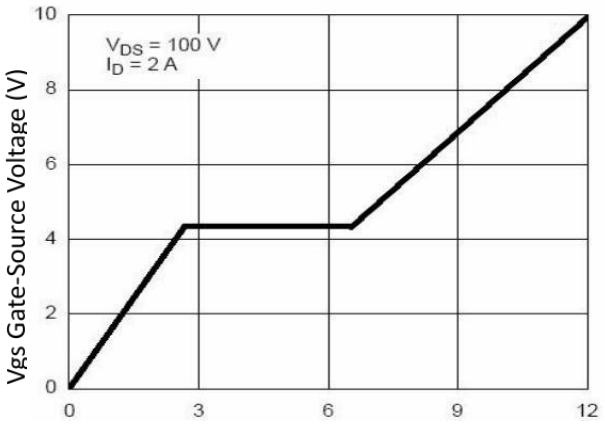
I_D - Drain Current (A)

Figure 3 Rdson- Drain Current



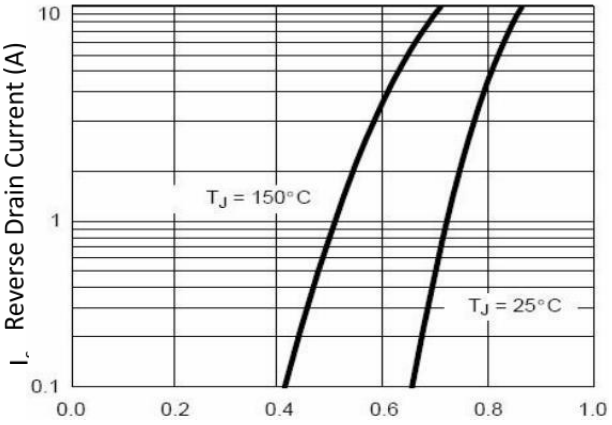
T_J -Junction Temperature (℃)

Figure 4 Rdson-JunctionTemperature



Qg Gate Charge (nC)

Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

Typical Characteristics

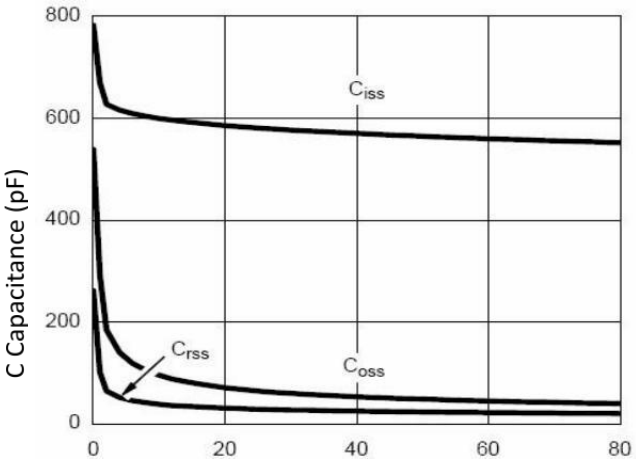


Figure 7 Capacitance vs Vds

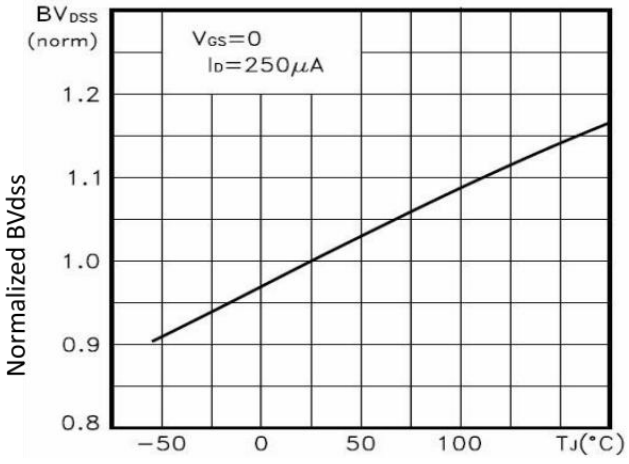


Figure 9 BV_{DSS} vs Junction Temperature

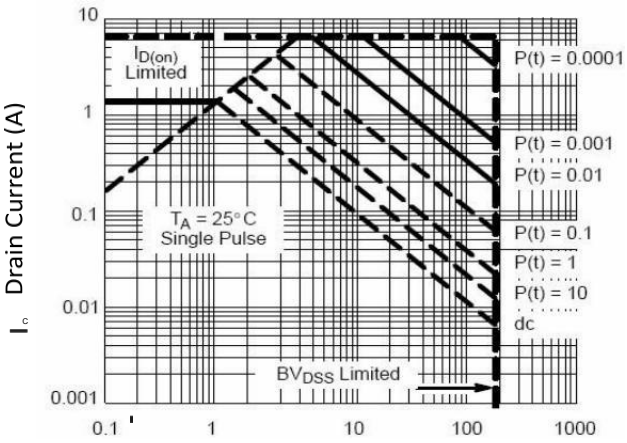


Figure 8 Safe Operation Area

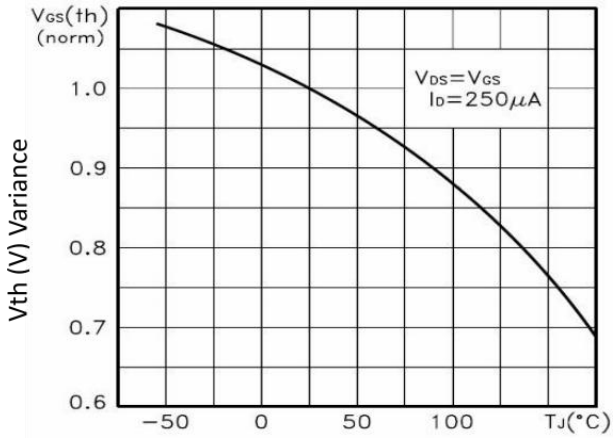


Figure 10 $V_{GS(th)}$ vs Junction Temperature

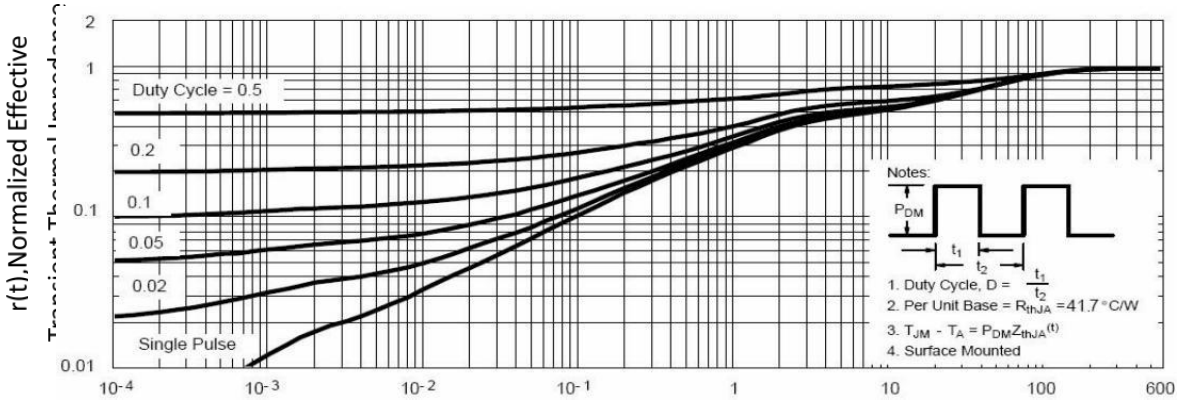
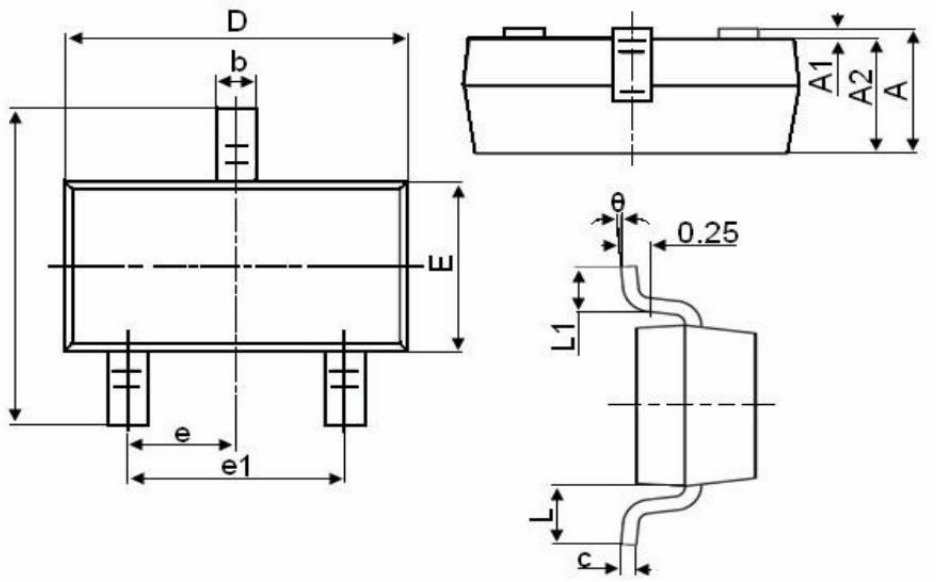


Figure 11 Normalized Maximum Transient Thermal Impedance

Package Mechanical Data：SOT23-3L



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e		0.950TYP
e1	1.800	2.000
L		0.550REF
L1	0.300	0.500
θ	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT-23-3L		3000